

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of: Gehrke, Thomas

Serial Number: Not Assigned

Filed: Concurrently Herewith

For: PENDEOEPIITAXIAL METHODS OF FABRICATING GALLIUM NITRIDE  
SEMICONDUCTOR LAYERS ON SAPPHIRE SUBSTRATES, AND GALLIUM NITRIDE  
SEMICONDUCTOR STRUCTURES FABRICATED THEREBY

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**INFORMATION DISCLOSURE STATEMENT  
UNDER 37 C.F.R. § 1.56 AND 37 C.F.R. § 1.97**

It is respectfully requested that the documents listed on the attached Form PTO/SB/08A be considered by the Patent and Trademark Office in the above-referenced application and made of record therein. A full text copy of the relevant documents have been previously disclosed in the parent application Ser. No. 09/899,586. This information disclosure statement submitted herewith is being filed within three months of the filing date of the application or date of entry into the national stage of an international application or before the mailing date of a first Office action on the merits, whichever event occurs last.

Respectfully submitted,

By:



Steven B. Phillips  
Registration No. 37,911  
Attorney for Applicant  
Moore & Van Allen, PLLC  
2200 West Main Street, Suite 800  
Durham, NC 27705  
Phone: 919-286-8000  
Facsimile: 919-286-8199

1/23/04  
Date

LIST OF DOCUMENTS CITED BY APPLICANT  
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Gehrke et al.Filing Date:  
November 17, 1999GAU:  
2812

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